# **ON Semiconductor**

## Is Now



To learn more about onsemi™, please visit our website at www.onsemi.com

onsemi and ONSEMI. and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. onsemi reserves the right to make changes at any time to any products or information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/ or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use onsemi products for any such unintended or unauthorized application,

# **Silicon Carbide Schottky Diode**

650 V, 10 A

# FFSM1065A

### **Description**

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

#### **Features**

- Max Junction Temperature 175°C
- Avalanche Rated 47 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery/No Forward Recovery
- This Device is Pb–Free, Halogen Free/BFR Free and RoHS Compliant

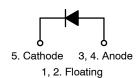
#### **Applications**

- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits

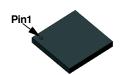


## ON Semiconductor®

www.onsemi.com



#### **Schottky Diode**





PQFN 8×8, 2P CASE 483AP

#### **MARKING DIAGRAM**

\$Y&Z&3&K FFSM 1065A

\$Y = ON Semiconductor Logo &Z = Assembly Plant Code &3 = Numeric Date Code &K = Lot Code

FFSM1065A = Specific Device Code

#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 2 of this data sheet.

#### FFSM1065A

## ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C unless otherwise noted)

Symbol	Parameter		Value	Unit
$V_{RRM}$	Peak Repetitive Reverse Voltage		650	V
E <sub>AS</sub>	Single Pulse Avalanche Energy (Note 1)		47	mJ
l <sub>F</sub>	Continuous Rectified Forward Current @ T <sub>C</sub> < 140°C		10	Α
	Continuous Rectified Forward Current @ T <sub>C</sub> < 135°C		11	
I <sub>F, Max</sub>	Non-Repetitive Peak Forward Surge Current	T <sub>C</sub> = 25°C, 10 μs	600	Α
		T <sub>C</sub> = 150°C, 10 μs	580	Α
I <sub>F,SM</sub>	Non-Repetitive Forward Surge Current	Half-Sine Pulse, t <sub>p</sub> = 8.3 ms	56	Α
I <sub>F,RM</sub>	Repetitive Forward Surge Current	Half-Sine Pulse, t <sub>p</sub> = 8.3 ms	28	Α
Ptot	Power Dissipation	T <sub>C</sub> = 25°C	71	W
		T <sub>C</sub> = 150°C	12	W
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

## THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{ hetaJC}$	Thermal Resistance, Junction to Case, Max	2.1	°C/W

## **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Тур	Max	Unit
V <sub>F</sub>	Forward Voltage	I <sub>F</sub> = 10 A, T <sub>C</sub> = 25°C	_	1.50	1.75	V
		I <sub>F</sub> = 10 A, T <sub>C</sub> = 125°C	_	1.6	2.0	
		I <sub>F</sub> = 10 A, T <sub>C</sub> = 175°C	_	1.72	2.4	
I <sub>R</sub>	Reverse Current	$V_R = 650 \text{ V}, T_C = 25^{\circ}\text{C}$	-	-	200	μΑ
		$V_R = 650 \text{ V}, T_C = 125^{\circ}\text{C}$	-	-	400	
		$V_R = 650 \text{ V}, T_C = 175^{\circ}\text{C}$	-	-	600	
$Q_{C}$	Total Capacitive Charge	V = 400 V	-	34	-	nC
С	Total Capacitance	V <sub>R</sub> = 1 V, f = 100 kHz	-	575	-	pF
		V <sub>R</sub> = 200 V, f = 100 kHz	-	62	-	
		V <sub>R</sub> = 400 V, f = 100 kHz	_	47	-	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

#### PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Shipping <sup>†</sup>
FFSM1065A	FFSM1065A	PQFN 8x8, 2P (Halogen Free)	3000Units / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>1.</sup>  $E_{AS}$  of 47 mJ is based on starting  $T_J = 25^{\circ}C$ , L = 1 mH,  $I_{AS} = 9.7$  A, V = 50 V.

## FFSM1065A

## **TYPICAL CHARACTERISTICS**

(T<sub>J</sub> = 25°C unless otherwise noted)

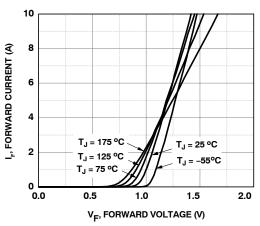


Figure 1. Forward Characteristics

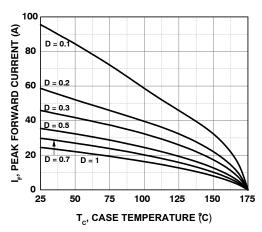


Figure 3. Current Derating

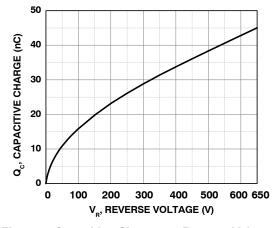


Figure 5. Capacitive Charge vs. Reverse Voltage

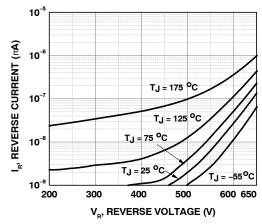


Figure 2. Reverse Characteristics

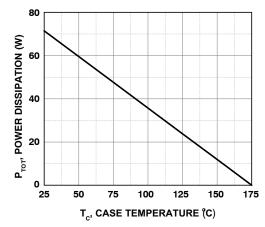


Figure 4. Power Derating

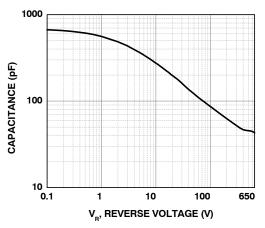


Figure 6. Capacitance vs. Reverse Voltage

## FFSM1065A

### **TYPICAL CHARACTERISTICS**

 $(T_J = 25^{\circ}C \text{ unless otherwise noted})$ 

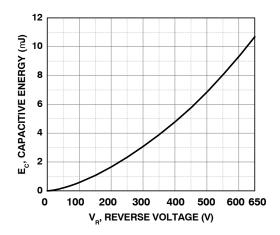


Figure 7. Capacitance Stored Energy

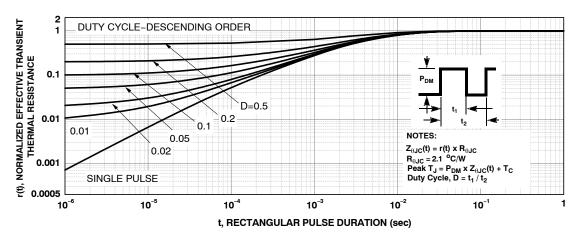


Figure 8. Junction-to-Case Transient Thermal Response Curve

## **TEST CIRCUIT AND WAVEFORMS**

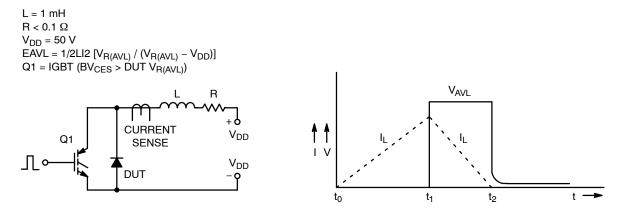
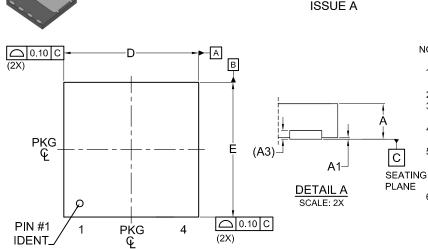


Figure 9. Unclamped Inductive Switching Test Circuit & Waveform



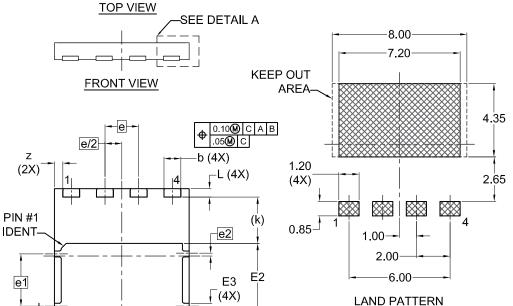


PQFN4 8X8, 2P CASE 483AP ISSUE A

**DATE 06 JUL 2021** 

#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. COPLANARITY APPLIES TO THE EXPOSED PADS AS WELL AS THE TERMINALS.
- 4. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
- SEATING PLANE IS DEFINED BY THE TERMINALS. "A1" IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.
- IT IS RECOMMENDED TO HAVE NO TRACES OR VIAS WITHIN THE KEEP OUT AREA.



(D3) (2X)

DIM	MILLIMETERS			
Diivi	MIN.	NOM.	MAX.	
Α	0.90	1.00	1.10	
A1	0.00	-	0.05	
А3	0.20 REF			
b	0.90	1.00	1.10	
D	7.90	8.00	8.10	
D2	7.10	7.20	7.30	
D3	0.40 REF			
E	7.90	8.00	8.10	
E2	4.25	4.35	4.45	
E3	0.25	0.35	0.45	
E4	0.40 REF			
е	2.00 BSC			
e/2	1.00 BSC			
e1	3.10 BSC			
e2	0.17 BSC			
k	2,75 REF			
L	0.40	0.50	0.60	

# RECOMMENDATION

\*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

DOCUMENT NUMBER:	98AON13664G	Electronic versions are uncontrolled except when accessed directly from the Document Reposito Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	PQFN4 8X8, 2P		PAGE 1 OF 1

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

D2

**BOTTOM VIEW** 

(E4)-

ON Semiconductor and the are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor and see no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and

#### **PUBLICATION ORDERING INFORMATION**

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com

ON Semiconductor Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative